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Texas Instruments CSD16413Q5A

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## CSD16413Q5A

SLPS199A-AUGUST 2009-REVISED APRIL 2010

## N-Channel NexFET<sup>™</sup> Power MOSFET

Check for Samples: CSD16413Q5A

### **FEATURES**

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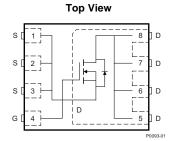
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- **Avalanche Rated**
- **Pb Free Terminal Plating**
- **RoHS Compliant**
- **Halogen Free**
- SON 5mm × 6mm Plastic Package

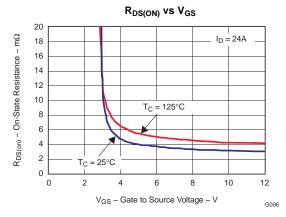
### **APPLICATIONS**

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and **Computing Systems**
- **Optimized for Control or Synchronous FET** Applications

### DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





### **PRODUCT SUMMARY**

V <sub>DS</sub>	Drain to Source Voltage 25				
Qg	Gate Charge Total (4.5V)	9	9		
Q <sub>gd</sub>	Gate Charge Gate to Drain	2.5	nC		
<b>_</b>	Drain to Source On Desistance	$V_{GS} = 4.5V$	4.1	mΩ	
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V$	3.1	mΩ	
V <sub>GS(th)</sub>	Threshold Voltage	1.6	V		

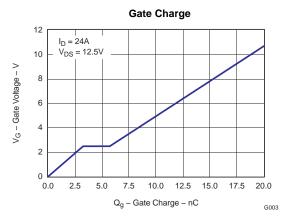
#### **ORDERING INFORMATION**

Device	Package	Media	Qty	Ship
CSD16413Q5A	SON 5 × 6 Plastic Package	13-inch reel	2500	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT					
$V_{\text{DS}}$	Drain to Source Voltage	25	V					
$V_{GS}$	Gate to Source Voltage	+16 / -12	V					
	Continuous Drain Current, $T_C = 25^{\circ}C$	100	А					
ID	Continuous Drain Current <sup>(1)</sup>	24	А					
I <sub>DM</sub>	Pulsed Drain Current, $T_A = 25^{\circ}C^{(2)}$	156	А					
PD	Power Dissipation <sup>(1)</sup>	3.1	W					
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C					
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D = 46A$ , L = 0.1mH, $R_G = 25\Omega$	106	mJ					

(1)  $R_{0.1A} = 41^{\circ}C/W$  on  $1in^2$  Cu (2 oz.) on 0.060" thick FR4 PCB. (2) Pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$ 



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## **ELECTRICAL CHARACTERISTICS**

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	haracteristics					
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = 20V$			1	μA
I <sub>GSS</sub>	Gate to Source Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = +16/-12V			100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.2	1.6	1.9	V
_	Davia da Causa da Daviatar da	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 24A		4.1	5.6	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = 10V, I_D = 24A$		3.1	3.9	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15V, I <sub>D</sub> = 24A		95		S
Dynamic	Characteristics					
C <sub>ISS</sub>	Input Capacitance			1370	1780	pF
C <sub>OSS</sub>	Output Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 12.5V f = 1MHz		1060	1380	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			84	109	pF
Rg	Series Gate Resistance			0.9	1.8	Ω
Qg	Gate Charge Total (4.5V)			9	11.7	nC
Q <sub>gd</sub>	Gate Charge Gate to Drain			2.5		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	V <sub>DS</sub> = 12.5V, I <sub>D</sub> = 24A		3.5		nC
Qg(th)	Gate Charge at Vth			2.2		nC
Q <sub>OSS</sub>	Output Charge	V <sub>DS</sub> = 13.1V, V <sub>GS</sub> = 0V		21		nC
t <sub>d(on)</sub>	Turn On Delay Time			9.1		ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 12.5V, V <sub>GS</sub> = 4.5V I <sub>D</sub> = 24A		15.9		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 5\Omega$		10.7		ns
t <sub>f</sub>	Fall Time			5.7		ns
Diode Cl	haracteristics					
V <sub>SD</sub>	Diode Forward Voltage	$I_{\rm S} = 24 {\rm A}, V_{\rm GS} = 0 {\rm V}$		0.85	1	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{DD}$ = 13.1V, I <sub>F</sub> = 24A, di/dt = 300A/µs		32		nC
t <sub>rr</sub>	Reverse Recovery Time	V <sub>DD</sub> = 13.1V, I <sub>F</sub> = 24A, di/dt = 300A/µs		28		ns

### THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Case <sup>(1)</sup>			2.6	°C/W
R <sub>0JA</sub>	Thermal Resistance Junction to Ambient <sup>(1) (2)</sup>			51	°C/W

 $R_{\theta JC}$  is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in .060 inch thick FR4 board.  $R_{\theta JC}$  is (1) specified by design while  $R_{\theta JA}$  is determined by the user's board design. Device mounted on FR4 Material with 1 inch<sup>2</sup> of 2 oz. Cu.

(2)



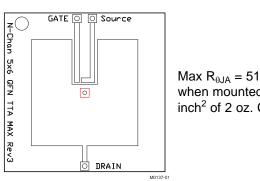
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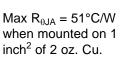
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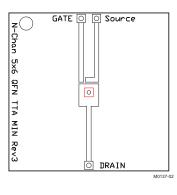
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Max  $R_{\theta JA} = 118^{\circ}C/W$ when mounted on minimum pad area of 2 oz. Cu.

### **TYPICAL MOSFET CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise stated)

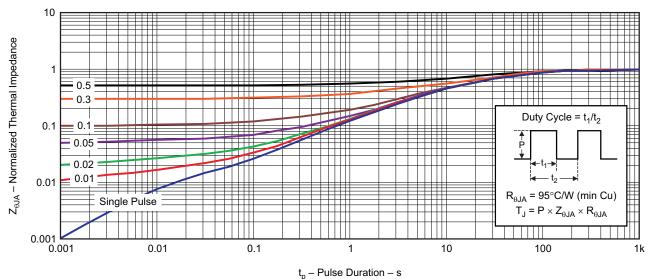


Figure 1. Transient Thermal Impedance

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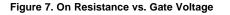
**TYPICAL MOSFET CHARACTERISTICS (continued)** (T<sub>A</sub> = 25°C unless otherwise stated) 80 80  $V_{DS} = 5V$ 70 70 10V V<sub>GS</sub> = 60 60 I<sub>D</sub> – Drain Current – A - Drain Current - A V<sub>GS</sub> = 4.5V  $V_{GS} = 3V$ 50 50  $T_C = 125^{\circ}C$ V<sub>GS</sub> = 3.5V 40 40  $T_C = 25^{\circ}C$ 30 30 ف 20 20 /<sub>GS</sub> = 2.5V  $T_C = -55^{\circ}C$ 10 10 0 0 0.0 0.5 1.0 1.5 2.0 2.5 3.0 1.0 1.5 2.0 2.5 3.0 3.5 4.0 V<sub>DS</sub> - Drain to Source Voltage - V VGS - Gate to Source Voltage - V G001 G002 Figure 2. Saturation Characteristics Figure 3. Transfer Characteristics 12 4.0  $I_D = 24A$ f = 1MHz3.5 V<sub>DS</sub> = 12.5V 10  $V_{GS} = 0V$ V<sub>G</sub> – Gate Voltage – V Ц 3.0 8 Capacitance -2.5  $C_{OSS} = C_{DS} + C_{GD}$  $C_{ISS} = C_{GD} + C_{GS}$ 6 2.0 1.5 4 с С 1.0  $C_{RSS} = C_{GD}$ 2 0.5 0 0.0 0.0 2.5 5.0 7.5 10.0 12.5 15.0 17.5 20.0 0 5 10 15 20 25 Qg - Gate Charge - nC V<sub>DS</sub> – Drain to Source Voltage – V G003 G004 Figure 4. Gate Charge Figure 5. Capacitance 2.5 20  $I_D = 250 \mu A$  $R_{DS(on)}$  – On-State Resistance – m $\Omega$  $I_D = 24A$ 18 V<sub>GS(th)</sub> – Threshold Voltage – V 2.0 16 14 1.5 12 10  $T_C = 125^{\circ}C$ 1.0 8 6 0.5 4 2  $T_C = 25^{\circ}C$ 0.0 0

> T<sub>C</sub> – Case Temperature – °C Figure 6. Threshold Voltage vs. Temperature

75

125

25



6

V<sub>GS</sub> – Gate to Source Voltage – V

2

4

0

-25

-75

4

8

10

12

G006

175

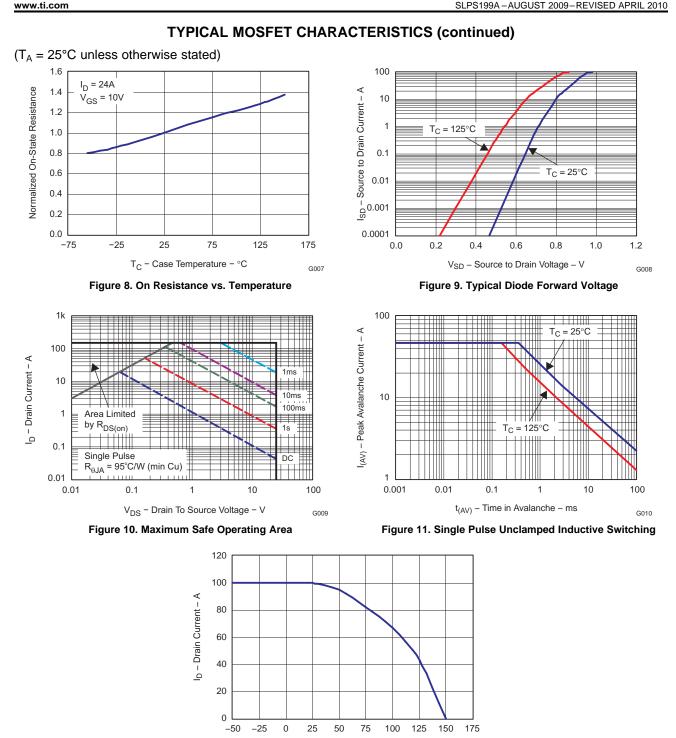
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#### T<sub>C</sub> – Case Temperature – °C G011 Figure 12. Maximum Drain Current vs. Temperature



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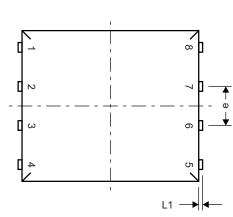
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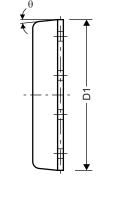


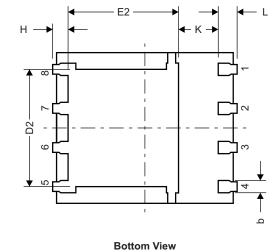
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**MECHANICAL DATA** 

### **Q5A Package Dimensions**



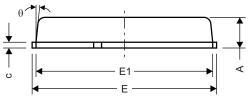




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Top View

Side View



Front View

M0135-01

DIM		MILLIMETERS							
	MIN	NOM	MAX						
A	0.90	1.00	1.10						
b	0.33	0.41	0.51						
С	0.20	0.25	0.30						
D1	4.80	4.90	5.00						
D2	3.61	3.81	3.96						
E	5.90	6.00	6.10						
E1	5.70	5.75	5.80						
E2	3.38	3.58	3.78						
е	1.27 BSC								
Н	0.41	0.51	0.61						
К	1.10								
L	0.51	0.61	0.71						
L1	0.06	0.13	0.20						
θ	0°		12°						



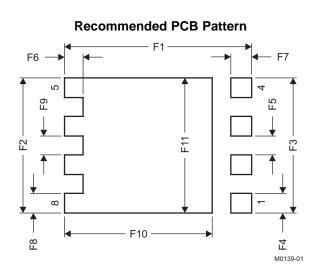
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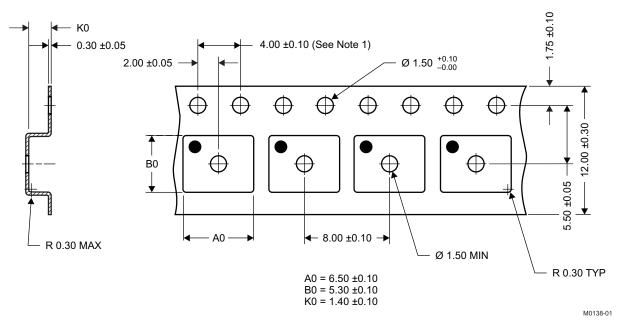
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DIM	MILLIN	IETERS	INCHES		
DIN	MIN	MAX	MIN	MAX	
F1	6.205	6.305	0.244	0.248	
F2	4.46	4.56	0.176	0.18	
F3	4.46	4.56	0.176	0.18	
F4	0.65	0.7	0.026	0.028	
F5	0.62	0.67	0.024	0.026	
F6	0.63	0.68	0.025	0.027	
F7	0.7	0.8	0.038	0.031	
F8	0.65	0.7	0.026	0.028	
F9	0.62	0.67	0.024	0.026	
F10	4.9	5	0.193	0.197	
F11	4.46	4.56	0.176	0.18	

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

### **Q5A Tape and Reel Information**



#### Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. A0 and B0 measured on a plane 0.3mm above the bottom of the pocket
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



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### **REVISION HISTORY**

Changes	from	Original	(August	2009)	to	Revision	Δ
Changes	nom	Unginal	(หน่งนอเ	2009)	ω	<b>VENI2IOII</b>	A

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PACKAGE OPTION ADDENDUM

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7-Jan-2016

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD16413Q5A	ACTIVE	VSONP	DQJ	8	2500	Pb-Free (RoHS	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16413	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs. LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available. OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above. Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight

in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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